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Title:Terahertz Current Oscillation in Wurtzite InN

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Abstract:Current self-oscillation in doped n - nn wurtzite InN diodes driven by a dc electric field is theoretically investigated by solving the time-dependent drift-diffusion model. Current self-oscillation is associated with the negative differential mobility effect in the highly non-parabolic conduction band of InN. A detailed analysis of the dependence of current oscillations on the doping concentration and the applied electric field is presented. The current oscillation frequencies can reach up to the terahertz (THz) region. The n - nn InN self-oscillating diode may be a promising candidate for THz generation, and the calculation results may guide the design of the devices.

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